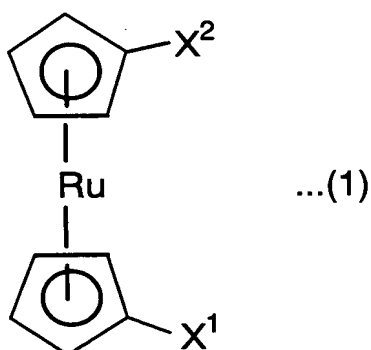


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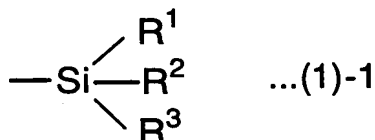
1. (Amended) A ruthenium compound for chemical vapor deposition which is at least one compound selected from the group consisting of a compound represented by the following

5 formula (1):



wherein X^1 and X^2 are each independently a hydrogen atom, fluorine atom, trifluoromethyl group, pentafluoroethyl

10 group or group represented by the following formula (1)-1:



wherein R^1 , R^2 and R^3 are each independently a hydrocarbon group having 1 to 10 carbon atoms,

15 with the proviso that X^1 and X^2 cannot be hydrogen atoms at the same time,

a compound represented by the following formula (2):



wherein R^4 is a trifluoromethyl group or hydrocarbon group having 1 to 10 carbon atoms, and three R^4 's may be the same or different,

and a compound represented by the following formula (4):



wherein Y is a cyclopentadienyl, cyclohexadienyl,

25 cycloheptadienyl, cyclooctadienyl, butadienyl or

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2,3-dimethyl-1,3-butadienyl group, L is a carbonyl group,
methyl group or ethenyl group, n is an integer of 1 to 4,
and m is an integer of 0 to 2, with the proviso that $n + m$
is 3 or 4, and two L's may be the same or different when m
5 is 2.

2. A process for producing a metal ruthenium film from
the ruthenium compound of claim 1 by chemical vapor
deposition.